



N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Fast Switching Speed
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- ESD Protected Gate 1kV
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

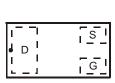
- Case: DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 5
- Ordering Information: See Page 5
- Weight: 0.001 grams (approximate)

DFN1006-3

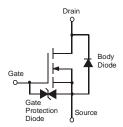




Bottom View



Top View Internal Schematic



Equivalent Circuit

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	25	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 3) Steady $T_A = 25^{\circ}\text{C}$ State $T_A = 85^{\circ}\text{C}$		I _D	1.3 0.9	А	
Pulsed Drain Current			I _{DM}	3.0	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3)	PD	0.54	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{θJA}	234	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. No purposefully added lead
- Diodes Inc's "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php
- 3. Device mounted on FR-4 substrate PCB board, with minimum recommended pad layout.

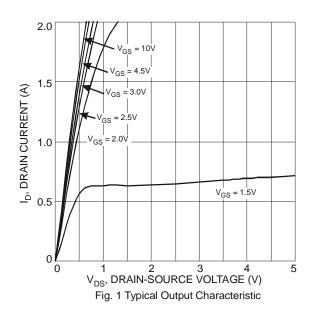


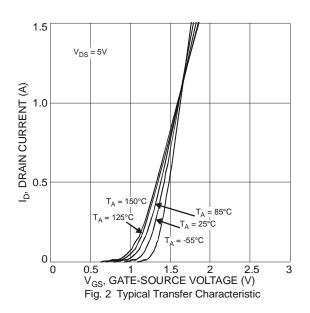
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	25	-	-	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	1	μΑ	$V_{DS} = 25V, V_{GS} = 0V$
Gate-Source Leakage	I_{GSS}	-	-	10	μΑ	$V_{GS} = \pm 8V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	0.45	-	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
				350		$V_{GS} = 4.5V, I_D = 200mA$
Static Drain-Source On-Resistance	R _{DS (ON)}	-	-	450	$m\Omega$	$V_{GS} = 2.5V, I_D = 100mA$
				600		$V_{GS} = 1.8V, I_D = 75mA$
Forward Transfer Admittance	Y _{fs}	40	-	-	mS	$V_{DS} = 3V, I_{D} = 200mA$
Diode Forward Voltage	V_{SD}	-	-	1.2	V	$V_{GS} = 0V, I_{S} = 300mA$
DYNAMIC CHARACTERISTICS (Note 5)						
Input Capacitance	C _{iss}	-	70.13	-	pF	15)/)/
Output Capacitance	Coss	-	7.56	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ -f = 1.0MHz
Reverse Transfer Capacitance	C_{rss}	-	5.59	-	pF	1 = 1.0WH2
Gate Resistance	R_g	-	72.3	-	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$
Total Gate Charge	Qq	-	0.85	-	nC	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\
Gate-Source Charge	Q _{gs}	-	0.16	-	nC	$V_{GS} = 4.5V, V_{DS} = 15V,$
Gate-Drain Charge	Q _{gd}	-	0.11	-	nC	-I _D = 1A
Turn-On Delay Time	t _{D(on)}	-	4.1	-	ns	
Turn-On Rise Time	t _r	-	11.5	-	ns	V_{DS} = 15V, R_L =15 Ω
Turn-Off Delay Time	t _{D(off)}	-	34.8	-	ns	$V_{GS} = 10V$, $R_G = 6\Omega$
Turn-Off Fall Time	t _f	-	20.9	-	ns	

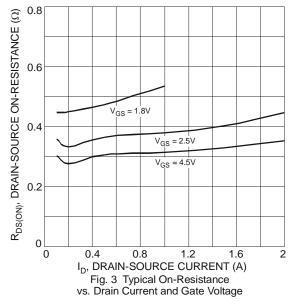
Notes: 4. Short duration pulse test used to minimize self-heating effect.

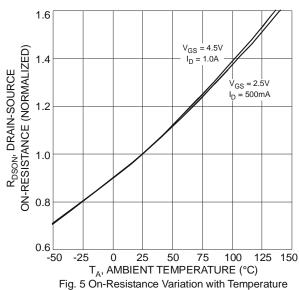
5. Guaranteed by design. Not subject to production testing.











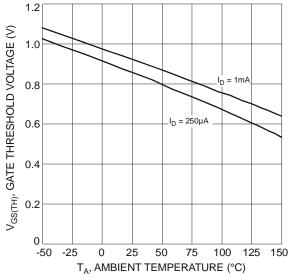
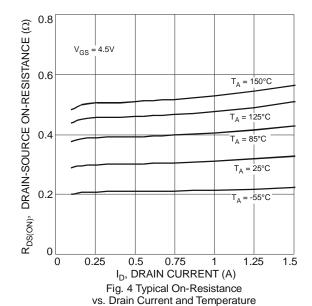


Fig. 7 Gate Threshold Variation vs. Ambient Temperature



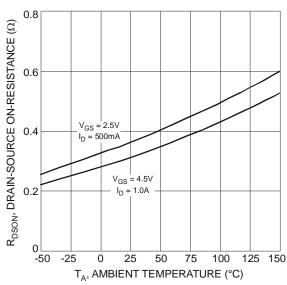
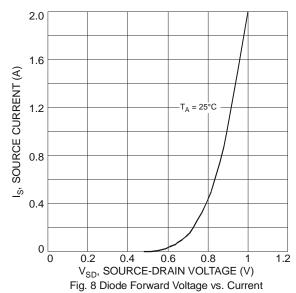
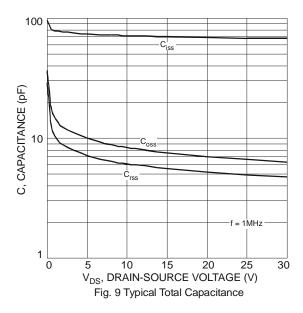
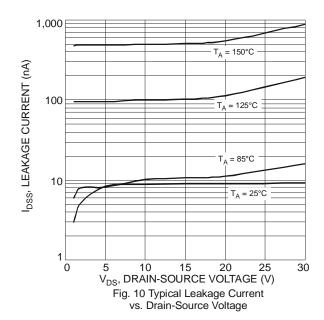


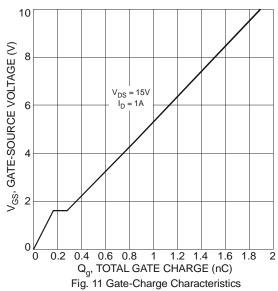
Fig. 6 On-Resistance Variation with Temperature

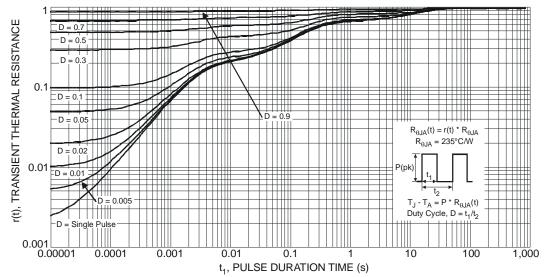














Ordering Information (Note 6)

Part Number	Case	Packaging
DMN2600UFB-7	DFN1006-3	3000/Tape & Reel

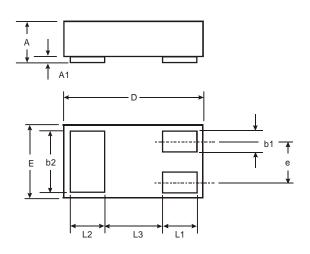
Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

• NA

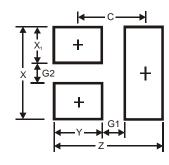
NA = Product Type Marking Code Dot Denotes Drain Side

Package Outline Dimensions



DFN1006-3			
Dim	Min	Max	Тур
Α	0.47	0.53	0.50
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
Е	0.55	0.675	0.60
е	_	_	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	_	_	0.40
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Υ	0.4
С	0.7



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